

Surface Mount Attenuator
30 Watts, 30dB



Features:

- RoHS Compliant
- 30 Watts
- Low Cost
- DC – 4.2 GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

Description:

The D30NA30Z4 is a high performance Aluminum Nitride (AlN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). The attenuator is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for inter-stage matching, directional couplers, and for use in isolators. The attenuator is also RoHS compliant!

General Specifications:

Resistive Element	Thick film
Substrate	AlN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +200°C (see de rating chart)

Electrical Specifications:

Attenuation Value:	30B	+1dB, -1dB; DC – 2.7GHz
		+1dB, -1.5dB, 2.7 – 3.0GHz
	28dB	+2dB, -2dB, 3.0 – 4.2GHz
Power:	30 Watts	
Frequency Range:	DC – 4.2GHz	
Input Return	20dB	DC – 3.0 GHz
Loss:	16dB	3.0 – 4.2 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

Outline Drawing:

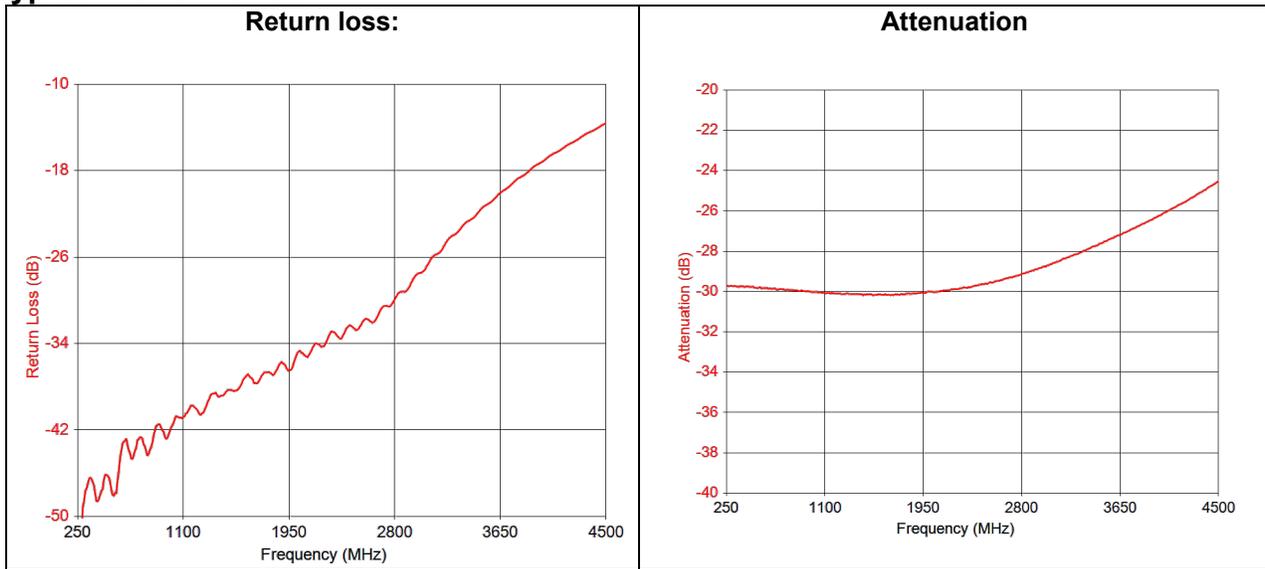
A	INPUT
B	OUTPUT
C/D	GROUND

Pad a can only be used as input, pad b can only be used as output

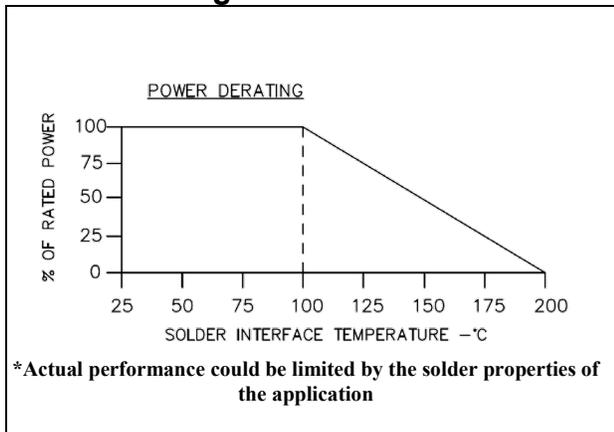
The bottom ground plane (c&d) is shown "split". This is only for manufacturing purposes. Pcb layout should be designed to have one continuous ground plane.

Tolerance is ± 0.010 ", unless otherwise specified. **All dimensions in inches.**

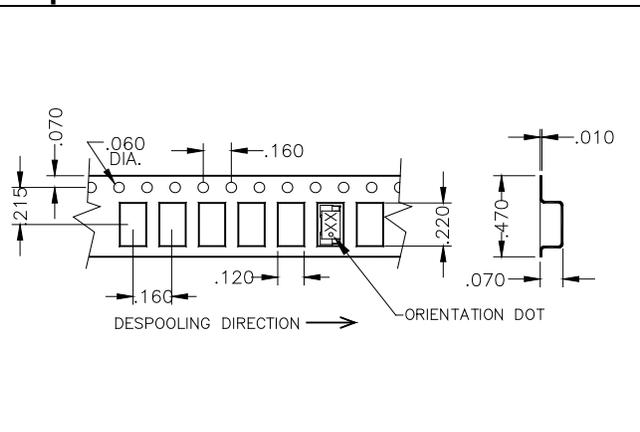
Typical Performance:



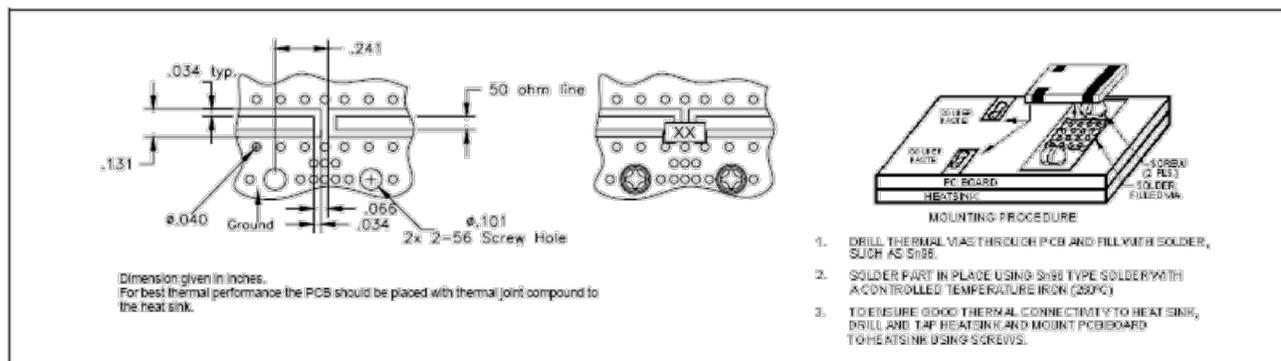
Power de-rating:



Tap & Reel:



Mounting Footprint:



Contact us:
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